



W22010A

256K × 4 HIGH SPEED CMOS STATIC RAM

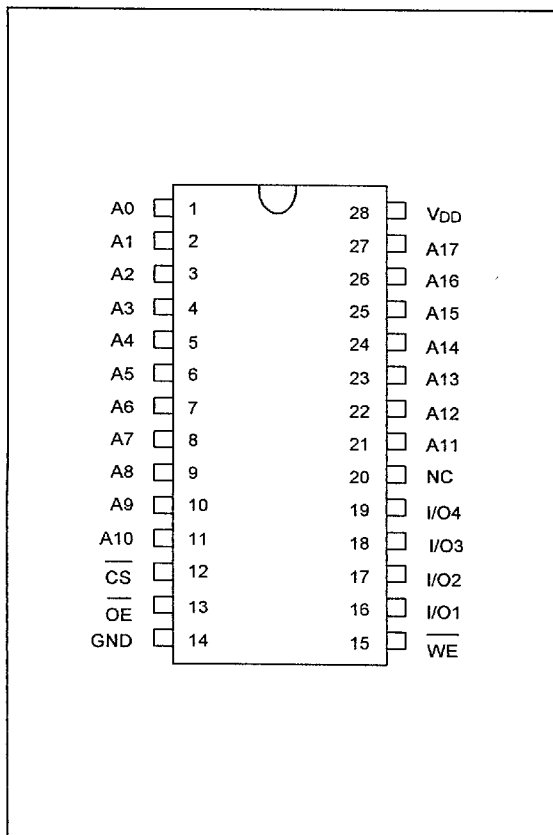
GENERAL DESCRIPTION

The W22010A is a high speed, low power CMOS static RAM organized as 262144 × 4 bits that operates on a single 5-volt power supply. This device is manufactured using Winbond's high performance CMOS technology.

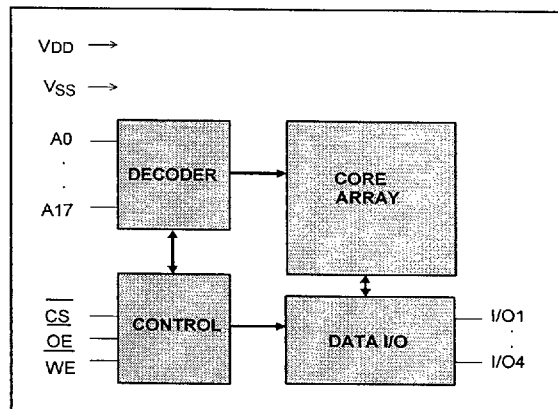
FEATURES

- High speed access time: 12/15/20 nS (max.)
- Low power consumption:
 - Active: 600 mW (typ.)
- Single +5V power supply
- Fully static operation
- All inputs and outputs directly TTL compatible
- Three-state outputs
- Available packages: 28-pin 300 mil SOJ and 400 mil SOJ

PIN CONFIGURATION



BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0-A17	Address Inputs
I/O1-I/O4	Data Inputs/Outputs
$\overline{CS}$	Chip Select Inputs
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
VDD	Power Supply
VSS	Ground
NC	No Connection

Publication Release Date: October 1996
Revision A3



TRUTH TABLE

CS	OE	WE	MODE	I/O1-I/O4	VDD CURRENT
H	X	X	Not Selected	High Z	ISB, ISB1
X	X	X	Not Selected	High Z	ISB, ISB1
L	H	H	Output Disable	High Z	IDD
L	L	H	Read	Data Out	IDD
L	X	L	Write	Data In	IDD

DC CHARACTERISTICS

Absolute Maximum Ratings

PARAMETER	RATING	UNIT
Supply Voltage to Vss Potential	-0.5 to +7.0	V
Input/Output to Vss Potential	-0.5 to VDD +0.5	V
Allowable Power Dissipation	1.0	W
Storage Temperature	-65 to +150	°C
Operating Temperature	0 to +70	°C

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

Operating Characteristics

(VDD = 5V ±10%, VSS = 0V, TA = 0 to 70°C)

PARAMETER	SYM.	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Input Low Voltage	V _{IL}	-		-0.5	-	+0.8	V
Input High Voltage	V _{IH}	-		+2.2	-	V _{DD} +0.5	V
Input Leakage Current	I _{LI}	V _{IN} = V _{SS} to V _{DD}		-10	-	+10	μA
Output Leakage Current	I _{LO}	V _{I/O} = V _{SS} to V _{DD} CS = V _{IH} (min.) or OE = V _{IH} (min.) or WE = V _{IL} (max.)		-10	-	+10	μA
Output Low Voltage	V _{OL}	I _{OL} = +8.0 mA		-	-	0.4	V
Output High Voltage	V _{OH}	I _{OH} = -4.0 mA		2.4	-	-	V
Operating Power	I _{DD}	CS = V _{IL} (max.), I/O = 0 mA	12	-	-	200	mA
Supply Current		Cycle = min	15	-	-	200	mA
		Duty = 100%	20	-	-	170	mA
Standby Power	I _{SB}	CS = V _{IH} (min.)		-	-	30	mA
Supply Current	I _{SB1}	CS ≥ V _{DD} -0.2V		-	-	10	mA

Note: Typical characteristics are at VDD = 5V, TA = 25°C.

CAPACITANCE

(V_{DD} = 5V, T_A = 25° C, f = 1 MHz)

PARAMETER	SYM.	CONDITIONS	MAX.	UNIT
Input Capacitance	C _{IN}	V _{IN} = 0V	8	pF
Input/Output Capacitance	C _{I/O}	V _{OUT} = 0V	10	pF

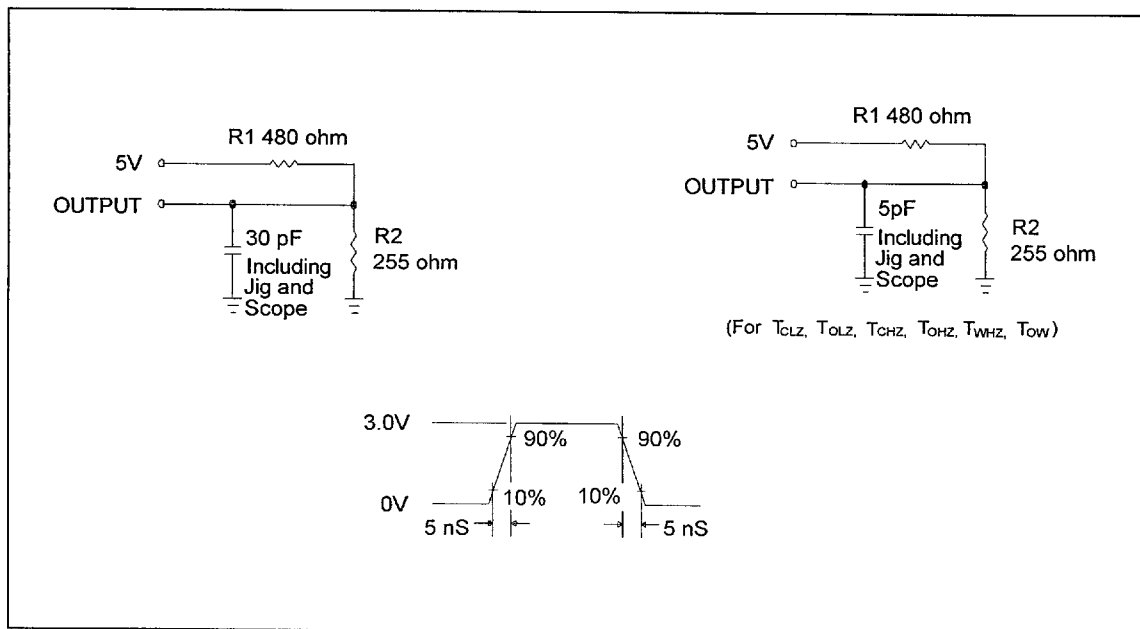
Note: These parameters are sampled but not 100% tested.

AC CHARACTERISTICS

AC Test Conditions

PARAMETER	CONDITIONS
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	5 nS
Input and Output Timing Reference Level	1.5V
Output Load	C _L = 30 pF, I _{OH} /I _{OL} = -4 mA/8 mA

AC Test Loads and Waveform



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AC Characteristics, continued

(VDD = 5V $\pm$ 10%, VSS = 0V, TA = 0 to 70° C)

Read Cycle

PARAMETER	SYM.	W22010A-12		W22010A-15		W22010A-20		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	TRC	12	-	15	-	20	-	nS
Address Access Time	TAA	-	12	-	15	-	20	nS
Chip Select Access Time	TACS	-	12	-	15	-	20	nS
Output Enable to Output Valid	TAOE	-	6	-	7	-	10	nS
Chip Selection to Output in Low Z	TCLZ*	3	-	3	-	3	-	nS
Output Enable to Output in Low Z	TOLZ*	0	-	0	-	0	-	nS
Chip Deselection to Output in High Z	TCHZ*	-	6	-	7	-	10	nS
Output Disable to Output in High Z	TOHZ*	-	6	-	7	-	10	nS
Output Hold from Address Change	TOH	3	-	3	-	3	-	nS

* These parameters are sampled but not 100% tested.

Write Cycle

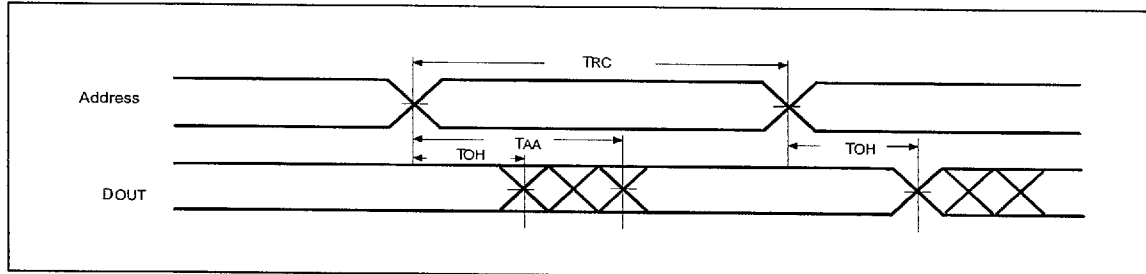
PARAMETER	SYM.	W22010A-12		W22010A-15		W22010A-20		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	TWC	12	-	15	-	20	-	nS
Chip Selection to End of Write	TCW	10	-	13	-	17	-	nS
Address Valid to End of Write	TAW	10	-	13	-	17	-	nS
Address Setup Time	TAS	0	-	0	-	0	-	nS
Write Pulse Width	TWP	10	-	10	-	12	-	nS
Write Recovery Time	TWR	0	-	0	-	0	-	nS
Data Valid to End of Write	TDW	7	-	9	-	10	-	nS
Data Hold from End of Write	TDH	0	-	0	-	0	-	nS
Write to Output in High Z	TWHZ*	-	7	-	8	-	10	nS
Output Disable to Output in High Z	TOHZ*	-	7	-	8	-	10	nS
Output Active from End of Write	TOW	0	-	0	-	0	-	nS

* These parameters are sampled but not 100% tested.

TIMING WAVEFORMS

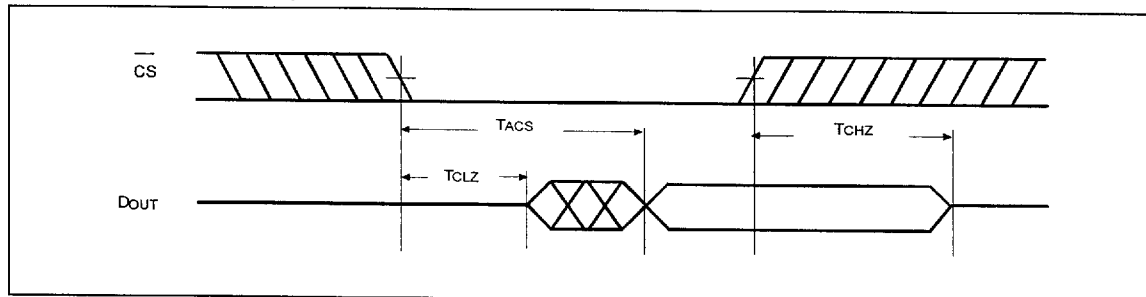
Read Cycle 1

(Address Controlled)



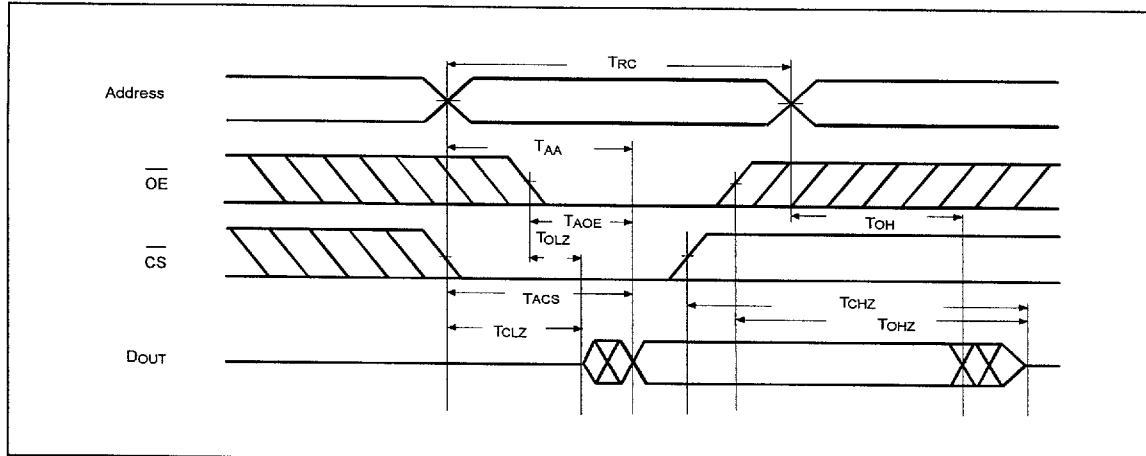
Read Cycle 2

(Chip Select Controlled)



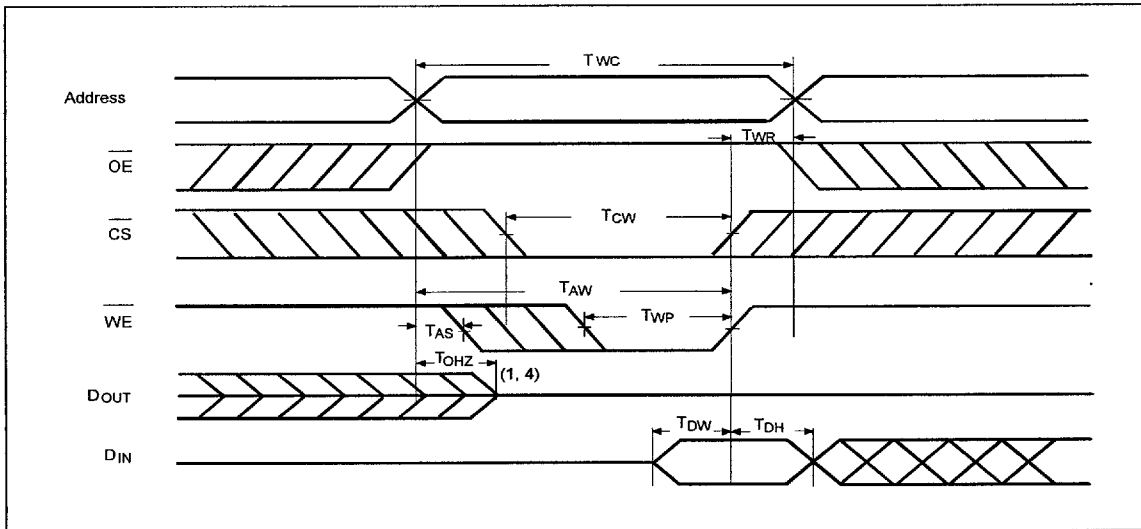
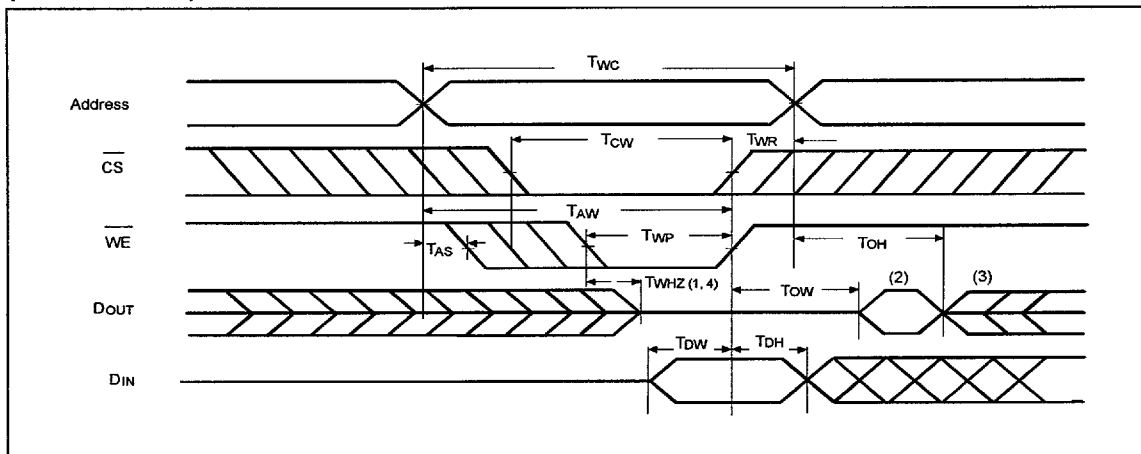
Read Cycle 3

(Output Enable Controlled)





Timing Waveforms, continued

Write Cycle 1**(OE Clock)****Write Cycle 2****(OE = VIL Fixed)****Notes:**

1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied
2. The data output from DOUT are the same as the data written to DIN during the write cycle.
3. DOUT provides the read data for the next address.
4. Transition is measured ± 500 mV from steady state with $C_L = 5$ pF. This parameter is guaranteed but not 100% tested.



W22010A

ORDERING INFORMATION

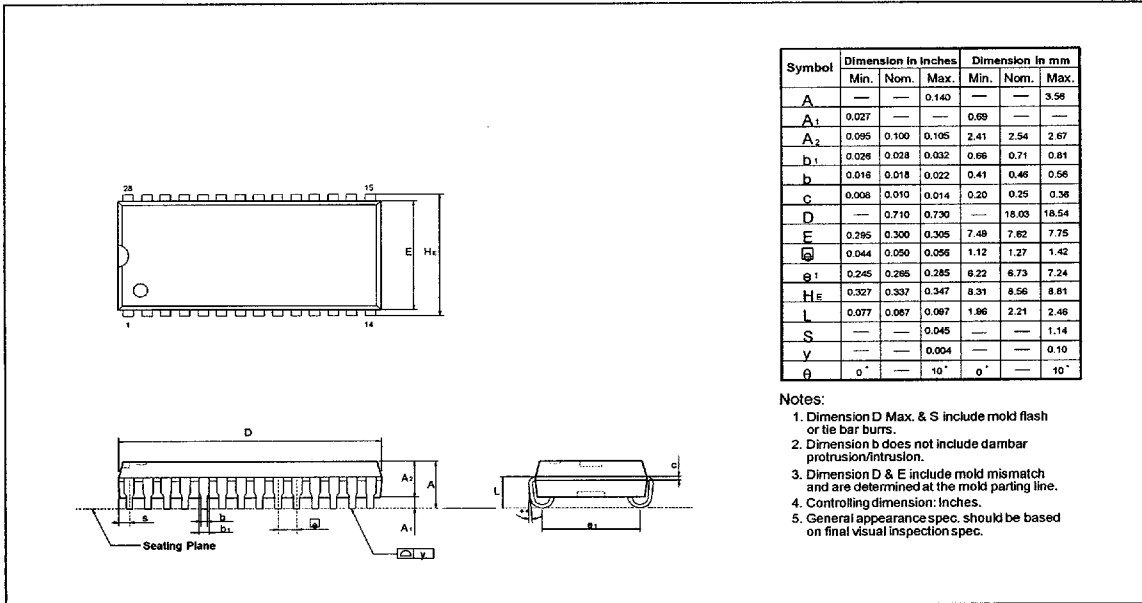
PART NO.	ACCESS TIME (nS)	OPERATING CURRENT MAX. (mA)	STANDBY CURRENT MAX. (mA)	PACKAGE
W22010AI-12	12	200	10	400 mil SOJ
W22010AI-15	15	200	10	400 mil SOJ
W22010AI-20	20	170	10	400 mil SOJ
W22010AJ-12	12	200	10	300 mil SOJ
W22010AJ-15	15	200	10	300 mil SOJ
W22010AJ-20	20	170	10	300 mil SOJ

Notes:

1. Winbond reserves the right to make changes to its products without prior notice.
2. Purchasers are responsible for performing appropriate quality assurance testing on products intended for use in applications where personal injury might occur as a consequence of product failure.

PACKAGE DIMENSIONS

28-pin SOJ (300 mil)



28-pin SOJ (400 mil)

